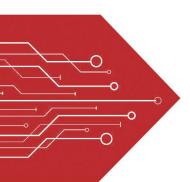
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet



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VOLTAGE RANGE 20 to 100 Volts CURRENT 5.0 Ampere



SMB

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Low forward voltage drop

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.093 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| P/N(MARK) | | SS52B | SS53B | SS54B | SS55B | SS56B | SS58B | SS59B | SS510B | UNITS |
|--|----------|------------|-------|-------|-------|-------|-------|-------|--------|-------|
| Maximum Recurrent Peak Reverse Voltage | | 20 | 30 | 40 | 50 | 60 | 80 | 90 | 100 | V |
| Maximum RMS Voltage | | 14 | 21 | 28 | 35 | 42 | 56 | 63 | 70 | V |
| Maximum DC Blocking Voltage | | 20 | 30 | 40 | 50 | 60 | 80 | 90 | 100 | V |
| Maximum Average Forward Rectified Current | | | | | | | | | | |
| at T∟=90 ℃ | | 5.0 | | | | | | Α | | |
| Peak Forward Surge Current, 8.3 ms single half sine-wave | | | | | | | | | | |
| superimposed on rated load (JEDEC method) | | 120 | | | | | | Α | | |
| Maximum Instantaneous Forward Voltage at 5.0A | | | 0.55 | | 0. | 70 | | 0.85 | | V |
| Maximum DC Reverse Current | Ta=25℃ | 0.1 0.02 | | | mA | | | | | |
| at Rated DC Blocking Voltage | Ta=100°C | | | 5 | | | | 2 | | mA |
| Typical Junction Capacitance (Note1) | | 380 | | | | | | pF | | |
| Typical Thermal Resistance R JL (Note 2) | | 16 | | | | | °C/W | | | |
| Operating Temperature Range T _J | | -65 —+150 | | | | | °C | | | |
| Storage Temperature Range Tsrc | | -65 — +150 | | | | | °C | | | |

NOTES:

- 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 2. Thermal Resistance Junction to Lead.

RATING AND CHARACTERISTIC CURVES (SS52B THRU SS510B)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

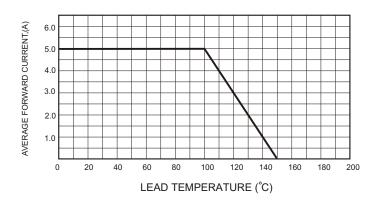


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

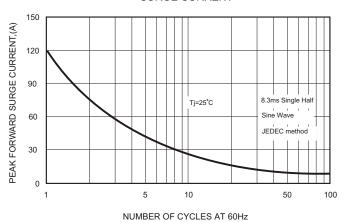
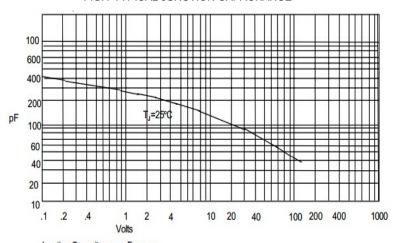


FIG.4-TYPICAL JUNCTION CAPACITANCE



Junction Capacitance - pF versus Reverse Voltage - Volts

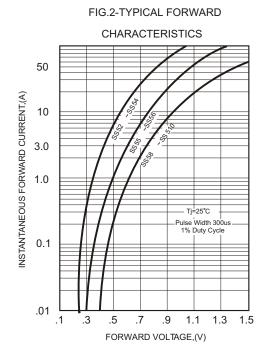
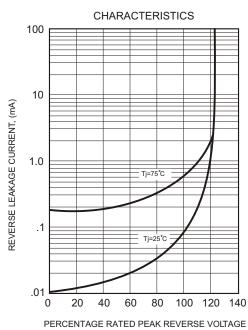
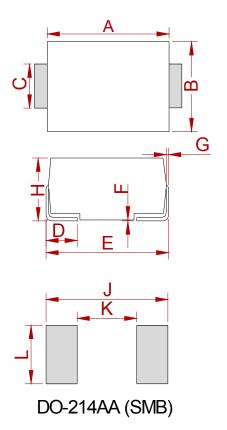


FIG.5 - TYPICAL REVERSE





PACKAGE MECHANICAL DATA



| | Dimensions | | | | | | |
|------|------------|--------|--------|-------|--|--|--|
| Ref. | Millir | neters | Inches | | | | |
| | Min. | Max. | Min. | Max. | | | |
| Α | 4.25 | 4.75 | 0.167 | 0.187 | | | |
| В | 3.30 | 3.94 | 0.130 | 0.155 | | | |
| С | 1.85 | 2.21 | 0.073 | 0.087 | | | |
| D | 0.76 | 1.52 | 0.030 | 0.060 | | | |
| Е | 5.08 | 5.59 | 0.200 | 0.220 | | | |
| F | 0.051 | 0.203 | 0.002 | 0.008 | | | |
| G | 0.15 | 0.31 | 0.006 | 0.012 | | | |
| Н | 2.11 | 2.44 | 0.083 | 0.096 | | | |
| J | 6.80 | | 0.270 | | | | |
| K | | 2.60 | | 0.100 | | | |
| L | 2.40 | | 0.090 | | | | |

REEL SPECIFICATION

| P/N | PKG | QTY |
|-------------------|-----|------|
| SS52B THRU SS510B | SMB | 3000 |



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